



**CHENMKO ENTERPRISE CO.,LTD**

*Lead free devices*

**SURFACE MOUNT  
Low Frequency PNP Transistor**

**VOLTAGE 12 Volts CURRENT 0.5 Ampere**

**2SA2119TPT**

**APPLICATION**

- \* For switching, for muting.

**FEATURE**

- \* Small surface mounting type. (SC-75/SOT-416)
- \* A collector current is large.
- \* Collector saturation voltage is low.  
 $V_{CE}(\text{sat}) \leq 250\text{mA}$   
At  $I_C = 200\text{mA}/I_B = 10\text{mA}$

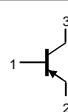
**CONSTRUCTION**

- \* PNP Silicon Transistor

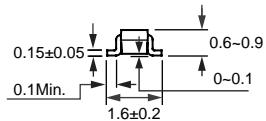
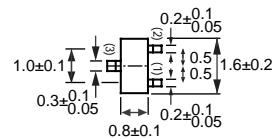
**MARKING**

- \* PU

**CIRCUIT**



**SC-75/SOT-416**



Dimensions in millimeters

**SC-75/SOT-416**

**MAXIMUM RATINGS ( At  $T_A = 25^\circ\text{C}$  unless otherwise noted )**

RATINGS	CONDITION	SYMBOL	MIN.	MAX.	UNITS
Collector - Base Voltage	Open Emitter	$V_{CBO}$	-	-15	Volts
Collector - Emitter Voltage	Open Base	$V_{CEO}$	-	-12	Volts
Collector Current DC		$I_C$	-	-500	mAmps
Peak Collector Current		$I_{CM}$	-	-1000	mAmps
Total Power Dissipation	$T_A \leq 25^\circ\text{C}; \text{ Note 1}$	$P_{TOT}$	-	150	mW
Storage Temperature		$T_{STG}$	-55	+150	°C
Junction Temperature		$T_J$	-	+150	°C
Operating Ambient Temperature		$T_{AMB}$	-55	+150	°C

**Note**

- Transistor mounted on ceramic substrate 50mmX50mmx0.8t.

## RATING CHARACTERISTICS ( 2SA2119TPT )

### **THERMAL CHARACTERISTICS CHARACTERISTICS**

$T_{amb} = 25^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	Typ.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$V_{CB}=-15\text{V}$	—	—	-0.1	$\mu\text{A}$
$BVCBO$	collector-base breakdown voltage	$I_C = -10\mu\text{A}$	-15	—	—	V
$BVCEO$	collector-emitter breakdown voltage	$I_C = -1\text{mA}$	-12	—	—	V
$BVEBO$	emitter-base breakdown voltage	$I_E = -10\mu\text{A}$	-6	—	—	V
$hFE$	DC current transfer ratio	$V_{CE}=-2\text{V}$ , $I_C=-10\text{mA}$	270	—	680	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C/I_B=-200\text{mA}/-10\text{mA}$	—	-100	-250	$\text{mV}$
$C_{ob}$	collector output capacitance	$I_E = 0$ ; $V_{CB} = -10\text{V}$ ; $f = 1 \text{ MHz}$	—	6.5	—	$\text{pF}$
$f_T$	transition frequency	$I_E = -10 \text{ mA}$ ; $V_{CE} = -2\text{V}$ ; $f = 30 \text{ MHz}$	—	260	—	$\text{MHz}$

### **Note**

1. Pulse test:  $t_p \leq 300 \mu\text{s}$ ;  $\delta \leq 0.02$ .

## RATING CHARACTERISTIC CURVES ( 2SA2119TPT )

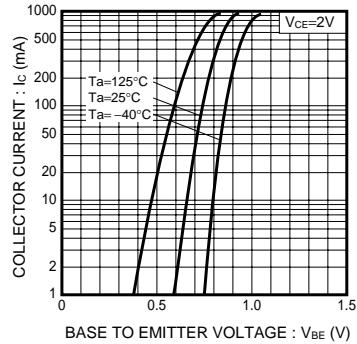


Fig.1 Grounded Emitter Propagation Characteristics

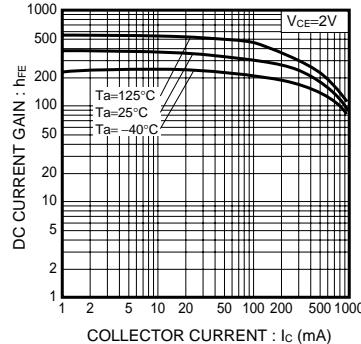


Fig.2 DC Current Gain vs. Collector Current

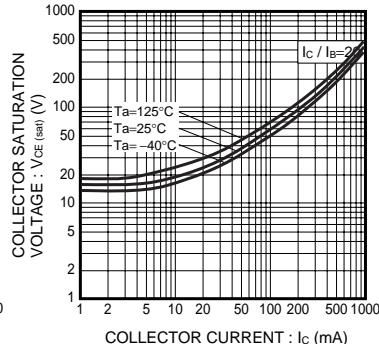


Fig.3 Collector-Emitter Saturation Voltage vs. Collector Current (I)

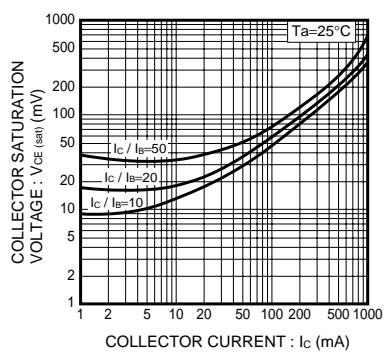


Fig.4 Collector-Emitter Saturation Voltage vs. Collector Current (II)

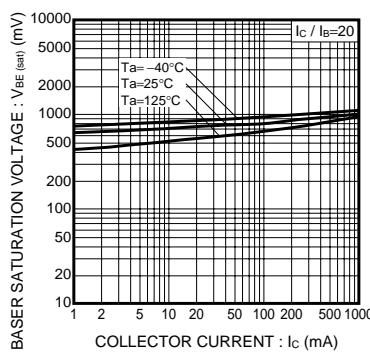


Fig.5 Base-Emitter Saturation Voltage vs. Collector Current

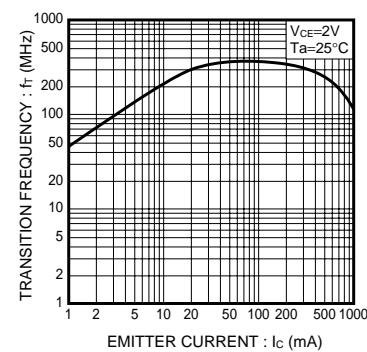


Fig.6 Gain Bandwidth Product vs. Emitter Current